

	Hits	Search Text	DBs
6	76	((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4) same (expos\$4 or illuminat\$4 or irradiat\$4)) and (post\$8imag\$4 or post\$5expos\$3) and (etch\$4 or RIE or (dry near5 etch\$4)) and ((metal\$4 or conductiv\$3 or TFT or LCD or (gate near6 electrode)) same (substrate or wafer) same (resist or photoresist) same (pattern\$4 or mask) same (post\$4etch\$4 or etch\$3 or RIE or (dry near4 etch\$4))) and ((expos\$4 or irradiat\$4 or illuminat\$4 or imag\$4) same (etch\$4 or RIE or post\$8etch) same (resist or photoresist) same (mask or pattern))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	11	((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4 or etch\$4) same (expos\$4 or illuminat\$4 or irradiat\$4)) and (post\$12imag\$4 or post\$9expos\$3) and (etch\$4 or RIE or (dry near\$5 etch\$4)) and ((metal\$4 or conductiv\$3 or TFT or LCD or (gate near\$6 electrode)) same (substrate or wafer) same (resist or photoresist) same (pattern\$4 or mask) same (post\$4etch\$4 or etch\$3 or RIE or (dry near\$4 etch\$4))) and ((expos\$4 or irradiat\$4 or illuminat\$4 or imag\$4) same (etch\$4 or RIE or post\$8etch) same (resist or photoresist) same (mask or pattern)) and ash\$4 and strip\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	11	((post\$3imag\$4 or post\$2expos\$3 or ((expos\$4 or irradiat\$4 or illuminat\$4) near\$16 (repeat\$4 or post) near\$16 (resist or photoresist) near\$12 pattern)) same ((subsequent or after or follow\$3) near\$9 etch\$4) near\$12 (metal\$3 or gate or insulat\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	11	((post\$3imag\$4 or post\$2expos\$3 or ((expos\$4 or irradiat\$4 or illuminat\$4) near16 (repeat\$4 or post) near16 (resist or photoresist) near12 pattern)) same ((subsequent or after or follow\$3) near9 (etch\$4 or RIE)) near12 (metal\$3 or gate or insulat\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	15	((post\$3imag\$4 or post\$2expos\$3 or ((expos\$4 or irradiat\$4 or illuminat\$4) near16 (repeat\$4 or post or unprocessed or deteriorated or residu\$4) near16 (resist or photoresist) near5 pattern)) same ((subsequent or after or follow\$3) near9 (etch\$4 or RIE)) near12 (metal\$3 or gate or insulat\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	52	430/328.ccls. and ((expos\$4 or post\$4imag\$4 or post\$4irradiat\$4 or post\$4expos\$4) same (resist or photoresist) same pattern\$3 same (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying) same (after or subsequent\$4 or sequential\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	23	430/328.ccls. and (((expos\$4 or post\$4imag\$4 or post\$4irradiat\$4 or post\$4expos\$4) near12 (resist or photoresist) near9 pattern\$3) same (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying) same (after or subsequent\$4 or sequential\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
13	5	430/328.ccls. and (((post\$4imag\$4 or ((post\$4 or after or subsequent) near9 (irradiat\$4 or expos\$4))) near12 (resist or photoresist) near9 pattern\$3) same (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying) same (after or subsequent\$4 or sequential\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	293	((post\$4imag\$4 or ((post\$4 or subsequent\$3) near9 (irradiat\$4 or expos\$4))) near12 (resist or photoresist) near6 pattern\$3) near16 (post\$4etch or etch\$4 or RIE) same (metal\$4 or gate or underlayer or underlying))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	123	((post\$4imag\$4 or ((post\$4 or subsequent\$3) near9 (irradiat\$4 or expos\$4))) near12 (resist or photoresist) near6 pattern\$3) near16 (post\$4etch or etch\$4 or RIE) near16 (metal\$4 or gate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	123	S16 NOT S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	34	S16 NOT S14 and ((resist or photoresist) same (thin\$4 or residu\$4) same (etch\$3 or post\$4etch\$4) same (expos\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
18	2	((resist or photoresist) near6 pattern\$4) same (thin\$4 or residu\$4) same (etch\$3 or post\$4etch\$4) same (subsequent\$4 near9 expos\$4) same (remov\$4 or strip\$4)) and ((metal\$4 or underlayer or gate) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE)) and (((resist or photoresist) near9 pattern\$3) same (post\$4expos\$4 or post\$4irradiat\$4 or post\$4illuminat\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	57	((resist or photoresist) near6 pattern\$4) same (thin\$4 or residu\$4) same (etch\$3 or post\$4etch\$4) same (subsequent\$4 near9 expos\$4) same (remov\$4 or strip\$4)) and ((metal\$4 or underlayer or gate) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE)) and (((resist or photoresist) near4 pattern\$3) same (contact\$4 or treat\$4) same (expos\$4 or UV or irradiation or radiation) same ((post\$4treat\$\$ or post\$4expos\$4 or subsequent\$4) near9 (illumination or expos\$4)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	73	((resist or photoresist) near6 pattern\$4) same (thin\$4 or residu\$4) same ((subsequent\$4 or post\$3) near9 (expos\$4 or irradiat\$4 or UV or illuminat\$4)) same strip\$4 same etch\$4) and ((metal\$4 or underl\$4 or gate or conductive or electrode) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
23	54	S23 NOT S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
24	14	((resist or photoresist) near16 pattern\$4) and post\$3imag\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
25	2	((resist or photoresist) near6 pattern\$4) and post\$3imag\$4 and (strip\$4 same etch\$4) and ((metal\$4 or underl\$4 or gate or conductive or electrode) same (resist or photoresist) same pattern\$4 same (etch\$4 or RIE))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
26	102	((resist or photoresist) near16 pattern\$4) and ((post\$3imag\$4 or expos\$4 or irradiat\$4 or illumiant\$4) near12 strip\$4 near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
27	42	((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illumiant\$4) near12 strip\$4 near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4)) same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
28	3	((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminant\$4) near12 (strip\$4 or remov\$4) near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4) near9 (UV or i\$4line or g\$3line or KrF or ArF or EUV or X\$2ray)) same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
29	3	((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminant\$4 or contact\$4 or treat\$4) near12 (strip\$4 or remov\$4) near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4) near9 (UV or i\$4line or g\$3line or KrF or ArF or EUV or X\$2ray)) same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
30	10	((resist or photoresist) near16 pattern\$4) and (((post\$3imag\$4 or expos\$4 or irradiat\$4 or illuminant\$4 or contact\$4 or treat\$4) near12 (strip\$4 or remov\$4) near16 (resist or photoresist) near4 pattern near12 (residu\$4 or remain\$4) near9 (UV or i\$4line or g\$3line or KrF or ArF or EUV or X\$2ray))) and ((resist or photoresist) same pattern same (etch\$4 or RIE) same (metal\$3 or conductive or underlayer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB